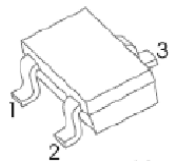
P-Channel MOSFET

SOT-23 Plastic-Encapsulate MOSFETS

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-30V	65mΩ@-10V	-4.1A
	75mΩ@-4.5V	
	85mΩ@-2.5V	

SOT-23



1. GATE
2. SOURCE
3. DRAIN

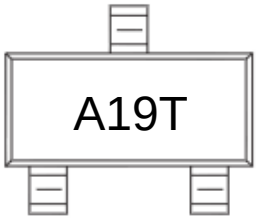
FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel

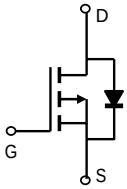
APPLICATION

- Interfacing , Switching

MARKING



Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	-4.1	A
Power Dissipation	P_D	350	mW
Thermal Resistance from Junction to Ambient (t<5s)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

Notes :

a. Surface Mounted on 1” ×1” FR4 board, t≤5s.

b. Pulse width limited by maximum junction temperature.

P-Channel MOSFET

ELECTRICAL CHARACTERISTICS (Ta= 25℃, unless otherwise specified.)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V,V_{GS} = 0V			-1	μA
Gate-source leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
On characteristics						
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =-10V, I_D =-4.2A		45	65	mΩ
		V_{GS} =-4.5V, I_D =-4A		60	80	mΩ
		V_{GS} =-2.5V,I_D=-1A		80	125	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =-5V, I_D =-5A	7			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.7		-1.3	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		954		pF
Output capacitance	C_{oss}			115		pF
Reverse transfer capacitance	C_{rss}			77		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_L=3.6Ω,R_{GEN}=6Ω			6.3	ns
Turn-on rise time	t_r				3.2	ns
Turn-off delay time	$t_{d(off)}$				38.2	ns
Turn-off fall Time	t_f				12	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 1)	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V

Notes :

a. Pulse Test : Pulse width≤300μs, duty cycle ≤2%.

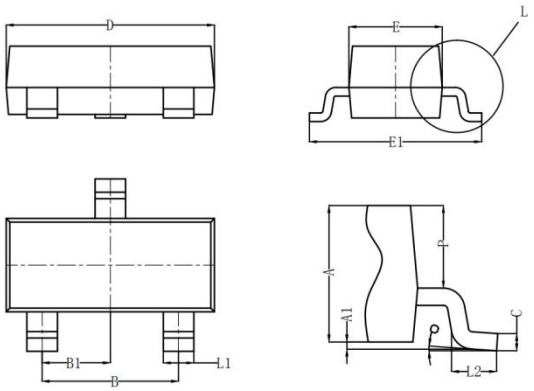
b. Guaranteed by design, not subject to production testing.

c. These parameters have no way to verify.

P-Channel MOSFET

Package Outline Dimensions

SOT23



Symbol	Dimensions (mm)		
	Min	Typ	Max
A	0.900	1.000	1.1100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950 Typ		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600

SOT-23 Suggested Pad Layout

